IN THE CLAIMS

Please amend the claims as follows:

- 1 (Currently Amended). A microcavity structure comprising two or more microcavity
- 2 | waveguides comprising photonic crystal structures, wherein one or more microcavity
- 3 active regions are created by the overlap of said microcavity waveguides and said two
- 4 or more microcavity waveguides comprise means for electrical activation.
- 2 (Original). The microcavity structure of claim 1, wherein said microcavity overlap is
- 2 defined by crossing of at least two of the said microcavity waveguide at an angle.
- 1 3 (Original). The microcavity structure of claim 1, wherein each waveguide includes at
- 2 least two optical reflectors.
- 4 (Currently Amended). The microcavity structure of claim 3 wherein the optical
- 2 reflector component comprises of a variation in material refractive index in order to
- 3 changes the direction of the incident optical energy.
- 5 (Original). The microcavity structure of claim 4 wherein the optical reflector could
- be, but is not restricted to, a structure with a periodic change in the refractive index
- 3 such as a photonic crystal.
- 6 (Original). The microcavity structure of claim 3, wherein the optical reflectors
- 2 surround the active microcavity regions.

- 7 (Currently Amended). The microcavity structure of claim 3, wherein one or more of
- 2 the optical reflectors are less reflective to define one or more output paths of the
- 3 generated light.
- 8 (Original). A microcavity structure of claim 1, wherein the microcavity waveguides
- 2 provide means for material continuity to achieve the conduction of current to the active
- 3 microcavity overlap regions.
- 1 9. (Cancelled).
- 1 10 (Previously Presented). The microcavity structure of claim 1 further comprising at
- least one contact pad that is coupled to each of the microcavity waveguides so as to
- 3 apply voltage across said microcavity structures.
- 1 11 (Original). The microcavity structure of claim 10, wherein the top waveguide
- 2 comprises p-doped material and the bottom waveguide comprises n-doped material.
- 1 12 (Original). The microcavity structure of claim 10, wherein the top waveguide
- comprises n-doped material and the bottom waveguide comprises p-doped material.
- 1 13 (Original). The microcavity structure of claim 1 further comprising a mechanism to
- 2 provide carrier confinement in the active overlap regions by converting the material
- 3 under portion of the upper waveguide into an insulator.
- 1 14 (Original). The microcavity structure of claim 1, wherein at least one of the
- 2 microcavity waveguides comprises active material used in the generation of photons.

- 1 15 (Original). A microcavity structure in claim 1, wherein the active material is
- 2 composed of quantum wells and/or quantum dots.
- 1 16 (Original). The microcavity structure of claim 1, wherein at least one of said
- 2 microcavity waveguides is used to guide light.
- 1 17 (Currently Amended). A method of forming a microcavity structure comprising:
- providing two or more microcavity waveguides comprising photonic crystal
- 3 structures; and
- forming one or more microcavity active regions by overlapping said microcavity
- 5 waveguides and said two or more microcavity waveguides comprise means for
- 6 electrical activation.
- 1 18 (Original). The method of claim 17, wherein said microcavity overlap is defined by
- 2 crossing of at least two of the said microcavity waveguide at an angle.
- 1 19 (Original). The method of claim 17, wherein each waveguide includes at least two
- 2 optical reflectors.
- 1 20 (Currently Amended). The method of claim 19, wherein the optical reflector
- 2 component comprises of a variation in material refractive index in order to changes the
- 3 direction of the incident optical energy.

- 1 21 (Original). The method of claim 20, wherein the optical reflector could be, but is
- 2 not restricted to, a structure with a periodic change in the refractive index such as a
- 3 photonic crystal.
- 1 22 (Original). The method of claim 19, wherein the optical reflectors surrounds the
- 2 active microcavity regions.
- 23 (Currently Amended). The method of claim 19, wherein one or more of the optical
- 2 reflectors are less reflective to define one or more output path of the generated light.
- 24 (Original). A method of claim 17, wherein the microcavity waveguides provide
- 2 means for material continuity to achieve the conduction of current to the active
- 3 microcavity overlap regions.
- 1 25. (Cancelled)
- 1 26 (Previously Presented). The method of claim 17 further comprising providing at
- 2 least one contact pad that is coupled to each of the microcavity waveguides so as to
- 3 apply voltage across said microcavity structures.
- 1 27 (Previously Presented). The method of claim 17, wherein the top waveguide
- 2 comprises p-doped material and said bottom waveguide comprises n-doped material.
- 1 28 (Previously Presented). The method of claim 17, wherein the top waveguide
- 2 comprises n-doped material and the bottom waveguide comprises p-doped material.

- 1 29 (Original). The method of claim 17 further comprising providing a mechanism to
- 2 provide carrier confinement in the active regions by converting the material under
- 3 portion of the upper waveguide into an insulator.
- 1 30 (Original). The microcavity structure of claim 17, wherein at least one of said first
- 2 and second waveguides comprises active material used in the generation of photons.
- 1 31 (Original). A microcavity structure in claim 17, wherein the active material is
- 2 composed of quantum wells and/or quantum dots.
- 32 (Original). The microcavity structure of claim 17, wherein at least one of said first
- 2 and second waveguides is used to guide light.
- 1 33 (Currently Amended). A microcavity structure comprising:
 - a first waveguide including a first photonic crystal microcavity comprising a first photonic crystal structure; and
 - a second waveguide including a second photonic crystal microcavity comprising a second photonic crystal structure; and
- a microcavity active region that is created by overlapping said first and second microcavities;
- wherein said first waveguide and second waveguide comprise means for
- 9 electrical activation.

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- 1 34 (Original). The microcavity of claim 33, wherein the photonic crystal surrounds the
- 2 active microcavity region.

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- 1 35 (Currently Amended). The microcavity structure of claim 33, wherein one or more
- 2 of the photonic crystals are less reflective to define a single or multiple output path of
- 3 the generated light.
- 1 36 (Original). The microcavity structure of claim 33, wherein the first and second
- 2 waveguides provide means for material continuity to achieve the conduction of current
- 3 to the active microcavity overlap region.
- 1 37. (Cancelled)
- 1 38 (Previously Presented). The microcavity structure of claim 33 further comprising at
- 2 least one contact pad that is coupled to said first waveguide and at least one contact pad
- 3 that is coupled to said second waveguide so as to apply voltage across said microcavity
- 4 structure.
- 1 39 (Previously Presented). The microcavity structure of claim 33, wherein said first
- 2 waveguide comprises p-doped material and said second waveguide comprises n-doped
- 3 material.
- 1 40 (Previously Presented). The microcavity structure of claim 33, wherein said first
- 2 waveguide comprises n-doped material and said second waveguide comprises p-doped
- 3 material.
- 41 (Original). The microcavity structure of claim 33 further comprising a mechanism to
- 2 provide carrier confinement to the active region by converting the material under
- 3 portion of the upper waveguide into an insulator.

- 1 42 (Original). The microcavity structure of claim 33, wherein at least one of said first
- 2 and second waveguides is used to guide light.
- 1 43 (Original). The microcavity structure of claim 33, wherein at least one of said first
- 2 and second waveguides comprises active material used in the generation of photons.
- 1 44 (Original). The microcavity structure of claim 43, wherein said active material
- 2 comprises quantum wells and/or quantum dots.
- 45 (Original). The microcavity structure of claim 42, wherein said first waveguide
- 2 guides generated light and said second waveguide comprises active material used in the
- 3 generation of photons.
- 1 46 (Original). The microcavity structure of claim 45, wherein said active material
- 2 comprises quantum wells and/or quantum dots.
- 1 47 (Original). The microcavity structure of claim 45, wherein said first waveguide
- 2 comprises p-doped material and said second waveguide comprises n-doped material.
- 1 48 (Original). The microcavity structure of claim 45, wherein said first waveguide
- 2 comprises n-doped material said second waveguide comprises p-doped material.
- 1 49 (Original). The microcavity structure of claim 42, wherein said second waveguide
- 2 guides generated light and said first waveguide comprises active material used in the
- 3 generation of photons.

- 50 (Original). The microcavity structure of claim 49, wherein said active material
- 2 comprises quantum wells and/or quantum dots.
- 1 51 (Original). The microcavity structure of claim 49, wherein said first waveguide
- 2 comprises p-doped material and said second waveguide comprises n-doped material.
- 1 52 (Original). The microcavity structure of claim 49, wherein said first waveguide
- 2 comprises n-doped material said second waveguide comprises p-doped material.
- 53 (Previously Presented). A method of forming a microcavity structure comprising:
- forming a first waveguide including a first photonic crystal microcavity; and
- forming a second waveguide including a second photonic crystal microcavity;
- 4 and
- forming a microcavity active region that is created by overlapping said first
- 6 layer and second microcavities, wherein said first waveguide and second waveguide
- 7 comprise means for electrical activation.
- 54 (Original). The method of claim 53, wherein the photonic crystal surrounds the
- 2 active microcavity region.
- 55 (Currently Amended). The method of claim 53, wherein one or more of the photonic
- 2 | crystals are less reflective to define a single or multiple output path of the generated
- 3 light.

- 1 56 (Original). The method of claim 53, wherein the first and second waveguides
- 2 provide means for material continuity to achieve the conduction of current to the active
- 3 microcavity overlap region.
- 1 57. (Cancelled)
- 1 58 (Previously Presented). The method of claim 53 further comprising at least one
- 2 contact pad that is coupled to said first waveguide and at least one contact pad that is
- 3 coupled to said second waveguide so as to apply voltage across said microcavity
- 4 structure.
- 1 59 (Previously Presented). The method of claim 53, wherein said first waveguide
- comprises p-doped material and said second waveguide comprises n-doped material.
- 1 60 (Previously Presented). The method of claim 53, wherein said first waveguide
- 2 comprises n-doped material and said second waveguide comprises p-doped material.
- 1 61 (Original). The method of claim 53 further comprising a mechanism to provide
- 2 carrier confinement to the active region by converting the material under portion of the
- 3 upper waveguide into an insulator.
- 1 62 (Original). The method of claim 53, wherein at least one of said first and second
- 2 waveguides is used to guide light.
- 1 63 (Original). The microcavity structure of claim 53, wherein at least one of said first
- 2 and second waveguides comprises active material used in the generation of photons.

- 1 64 (Original). The microcavity structure of claim 63, wherein said active material
- 2 comprises quantum wells and/or quantum dots.
- 1 65 (Original). The microcavity structure of claim 62, wherein said first waveguide
- 2 guides generated light and said second waveguide comprises active material used in the
- 3 generation of photons.
- 1 66 (Original). The method of claim 65, wherein said active material comprises
- 2 quantum wells and/or quantum dots.
- 1 67 (Original). The method of claim 65, wherein said first waveguide comprises p-
- 2 doped material and said second waveguide comprises n-doped material.
- 1 68 (Original). The method of claim 65, wherein said first waveguide comprises n-
- 2 doped material said second waveguide comprises p-doped material.
- 1 69 (Original). The method of claim 62, wherein said second waveguide guides
- 2 generated light and said first waveguide comprises active material used in the
- 3 generation of photons.
- 1 70 (Original). The method of claim 69, wherein said active material comprises quantum
- 2 wells and/or quantum dots.
- 1 71 (Original). The method of claim 69, wherein said first waveguide comprises p-
- 2 doped material and said second waveguide comprises n-doped material.

1 72 (Original). The method of claim 69, wherein said first waveguide comprises n-

2 doped material said second waveguide comprises p-doped material.